

a plurality of integrated circuit dies fabricated on said wafer, each die comprising:

a first terminal coupled to the circuitry within said die for supplying said first voltage to said circuitry;

a second terminal for supplying said first voltage to said first terminal;

a voltage interruption device provided between first and second terminals for interrupting an electrical coupling between said first and second terminals; and

a first sacrificial terminal for receiving said first voltage from said first sacrificial conductive line and supplying said first voltage to said second terminal.

9. (Currently Amended) A semiconductor die comprising:

a Vcc bonding pad coupled to the circuitry within said die for supplying a first voltage to said circuitry;

a secondary Vcc bonding pad;

a fuse interconnected between the Vcc bonding pad and the secondary Vcc bonding pad, said secondary Vcc bonding pad supplying said first voltage through said fuse to the Vcc bonding pad, said fuse adapted for interrupting electrical coupling between the secondary Vcc bonding pad and said Vcc bonding pads when the die draws current in excess of said fuse breakdown current;

a sacrificial Vcc bonding pad for receiving said first voltage; and

a sacrificial metal bus interconnected between the sacrificial Vcc bonding pad and secondary Vcc bonding pad for receiving said first voltage from the sacrificial Vcc bonding pad and supplying said first voltage to the secondary Vcc bonding pad.

10. (Currently Amended) The semiconductor wafer of claim 9 further comprising:

a Vss bonding pad coupled to the circuitry within said die for supplying a second voltage to said circuitry;

a sacrificial Vss bonding pad for supplying the second voltage to the Vss bonding pad; and

a sacrificial metal bus which connects the sacrificial Vss bonding pad and the Vss bonding pad.

25. (Currently Amended) A semiconductor wafer comprising:

at least one first sacrificial conductive line for supplying a first voltage to a plurality of dies fabricated on said wafer;

a plurality of integrated circuit dies fabricated on said wafer, each die comprising:

a first terminal coupled to the circuitry within said die for supplying said first voltage to said circuitry;

a voltage interruption device coupled to said first terminal;

a second terminal coupled to said voltage interruption device, said interruption device for interrupting an electrical coupling between said first and second terminals; and

a first sacrificial terminal electrically coupled to said second terminal for receiving said first voltage from said first sacrificial conductive line and supplying said first voltage to said second terminal.